## Minoru Noda

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Labelâ€free, chronological and selective detection of aggregation and fibrillization of amyloid β protein in serum by microcantilever sensor immobilizing cholesterolâ€incorporated liposome. Biotechnology and Bioengineering, 2020, 117, 2469-2478.	3.3	4
2	A Cantileverâ€based Biosensor for Realâ€time Monitoring of Interactions between Amyloidâ€Î²(1–40) and Membranes Comprised of Phosphatidylcholine Lipids with Different Hydrophobic Acyl Chains. Electroanalysis, 2017, 29, 722-729.	2.9	4
3	A Label-Free Fluorescent Array Sensor Utilizing Liposome Encapsulating Calcein for Discriminating Target Proteins by Principal Component Analysis. Sensors, 2017, 17, 1630.	3.8	10
4	Detection of Amyloid Beta Fibril Growth by Liposome-Immobilized Micro-Cantilever With NiCr Thin-Film Strain Gauge. IEEE Sensors Journal, 2015, 15, 7135-7141.	4.7	9
5	Leakage current characteristics of new SrBi <inf>4</inf> Ti <inf>4</inf> O <inf>15</inf> /CaBi <inf>4</inf> Ti <ir thin-film capacitor with excellent electric stability. , 2013, , .</ir 	ıf>4<	;/inf>0<
6	A new SrBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> /CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> thin-film capacitor for excellent electric stability. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2012, 59, 1888-1893.	3.0	3
7	Resonant Frequency Tuning of Piezoelectric Ultrasonic Microsensors by Bias Voltage Application to Extra Top-Electrodes on PZT Diaphragms. Ferroelectrics, 2010, 408, 48-54.	0.6	12
8	Comparison of BST film microwave tunable devices based on (100) and (111) MgO substrates. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2010, 57, 2221-2227.	3.0	4
9	Fabrication and Characterization of Normal and Shear Stresses Sensitive Tactile Sensors by Using Inclined Micro-cantilevers Covered with Elastomer. Materials Research Society Symposia Proceedings, 2007, 1052, 1.	0.1	11
10	Low Temperature Preparation of Bismuth-Related Ferroelectrics by Hydrothermal Synthesis. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	2
11	LOW TEMPERATURE CRYSTALLIZATION OF Pb(Zr,Ti)O3 AND PbTiO3 MOCVD THIN FILM BY HYDROTHERMAL TREATMENT AT 240°C. Integrated Ferroelectrics, 2006, 84, 137-146.	0.7	1
12	Analysis of Complex Permittivity of Liposome for Its Biochemical Dynamics up to 30 GHz Range. , 2006, ,		7
13	PREPARATION AND CHARACTERIZATION OF NATURAL-SUPERLATTICE-STRUCTURED Bi2MoO6â <sup>^</sup> Bi4Ti3O12(m =	Tj ETQq1 0.7	1 <b>0.78431</b> 4
14	An Application of a Low-Loss MOD-Made BST Film Developed Especially with PLD Initial Nucleation Layer to a 20 GHz Tunable Phase Shifter. Materials Research Society Symposia Proceedings, 2004, 833, 33.	0.1	0
15	A Highly-Sensitive Ba(Ti1—xSnx)O3 Thin Film Dielectric Bolometer for Uncooled IR Sensor. Integrated Ferroelectrics, 2004, 63, 35-40.	0.7	10
16	Nitridation of Ultrathin SiO2 Layers in Metal-Ferroelectric-Insulator-Semiconductor Structures. Integrated Ferroelectrics, 2004, 68, 29-36.	0.7	1
17	Polarization Hysteresis Control by La and Nd Substitutions in Natural-Superlatice-Structured Bi3TiNbO9-Bi4Ti3O12 Thin Films. Integrated Ferroelectrics, 2004, 65, 149-157.	0.7	0
18	Low Temperature Preparation of Functional Oxide Thin Film by Sol-gel-Hydrothermal Process-Application to Si ULSI Monolithic Process for Large-Scale Integrated Sensor, Actuator, and Memory IEEJ Transactions on Sensors and Micromachines, 2004, 124, 203-206.	0.1	0

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19	Prominent ferroelectricity of BiFeO3 thin films prepared by pulsed-laser deposition. Applied Physics Letters, 2003, 83, 3981-3983.	3.3	215
20	Ferroelectric and Ferromagnetic Properties of BiFeO3 Thin Films Deposited by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 2003, 784, 11521.	0.1	0
21	Preparation and Characterization of Ferroelectric Bi3TiNbO9-Bi4Ti3O12 (m =2–3) Thin Films with Different Superlattice Structures. Materials Research Society Symposia Proceedings, 2003, 784, 181.	0.1	0
22	Basic characteristics of metal-ferroelectric-insulator-semiconductor structure using a high-k PrOx insulator layer. Journal of Applied Physics, 2003, 93, 4137-4143.	2.5	19
23	Preparation and basic properties of ferroelectric thin films having a superlattice structure of 2 Bi3TiNbO9 units–1 Bi4Ti3O12 unit. Applied Physics Letters, 2003, 83, 1411-1413.	3.3	20
24	A Very Low-Temperature Growth of BaTiO3 Thin Film by Hydrothermal Treatment Following Sol-Gel Coating at 200 Degree Celsius. Integrated Ferroelectrics, 2003, 52, 111-118.	0.7	3
25	Crystallization of BaTiO3Thin Film at 140°C by Metalorganic Decomposition Hydrothermal Method Using Different Precursors. Japanese Journal of Applied Physics, 2002, 41, 6619-6623.	1.5	13
26	X-ray Photoelectron and UV Photoyield Spectroscopic Studies on Structural and Electronic Properties of SrxBiyTa 209 Films. Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	0
27	Ferroelectric Bi4Ti3O12–SrBi4Ti4O15 Intergrowth Thin Films Prepared by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 2002, 748, 1.	0.1	0
28	X-ray Photoelectron and UV Photoyield Spectroscopic Studies on Structural and Electronic Properties of SrxBiyTa2O9 Films. Materials Research Society Symposia Proceedings, 2002, 748, 1.	0.1	0
29	Effect of leakage current through ferroelectric and insulator on retention characteristics of metal-ferroelectric-insulator-semiconductor structure. Integrated Ferroelectrics, 2001, 40, 125-134.	0.7	6
30	Crystallization of BaTiO3 Thin Films Prepared by Metalorganic Decomposition with Hydrothermal Treatment at 140°C. Materials Research Society Symposia Proceedings, 2001, 688, 1.	0.1	0
31	Lowâ—¡temperature preparation of baxsr1-xtio3 thin films prepared by sol-gel-hydrothermal method. Integrated Ferroelectrics, 2001, 36, 215-224.	0.7	1
32	Theoretical and Experimental Studies on Retention Characteristics of Metal-Ferroelectric-Insulator-Semiconductor and Metal-Insulator -Ferroelectric-Insulator-Semiconductor Structures. Materials Research Society Symposia Proceedings, 2000, 655, 154	0.1	2
33	Preparation and Characterization of MFM and MFIS Structures Using Sr2(Ta1å^'x, Nbx)2O7 Thin Film by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 2000, 655, 307.	0.1	1
34	A low temperature preparation of Sr0.7Bi2+x.Ta2O9thin films on SiO2/Si by pulsed laser deposition for application of metal-ferroelectric-insulator-semiconductor structure. Ferroelectrics, Letters Section, 1999, 26, 17-28.	1.0	1
35	Low Temperature Preparation of Sr2(Ta1-x, Nbx)2O7 Ferroelectric Thin Film by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 1999, 596, 185.	0.1	0
36	Oriented Sr0.48Ba0.51La0.01Nb2O6thin films prepared on Pt/Ti/SiO2/Si(100) substrate by pulsed laser deposition. Ferroelectrics, 1998, 219, 15-22.	0.6	0

#	Article	IF	CITATIONS
37	Preparation of Sr0.7Bi2+xTa2O9 Thin Films on SiO2/Si at Low Temperature by Pulsed Laser Deposition and Fatigue-Tolerant C-V Characteristics with Large Memory Window. Materials Research Society Symposia Proceedings, 1998, 541, 299.	0.1	1